

ANALYSIS AND OPTIMIZATION OF HF DC/DC CONVERTERS FOR RF POLAR TRANSMITTERS



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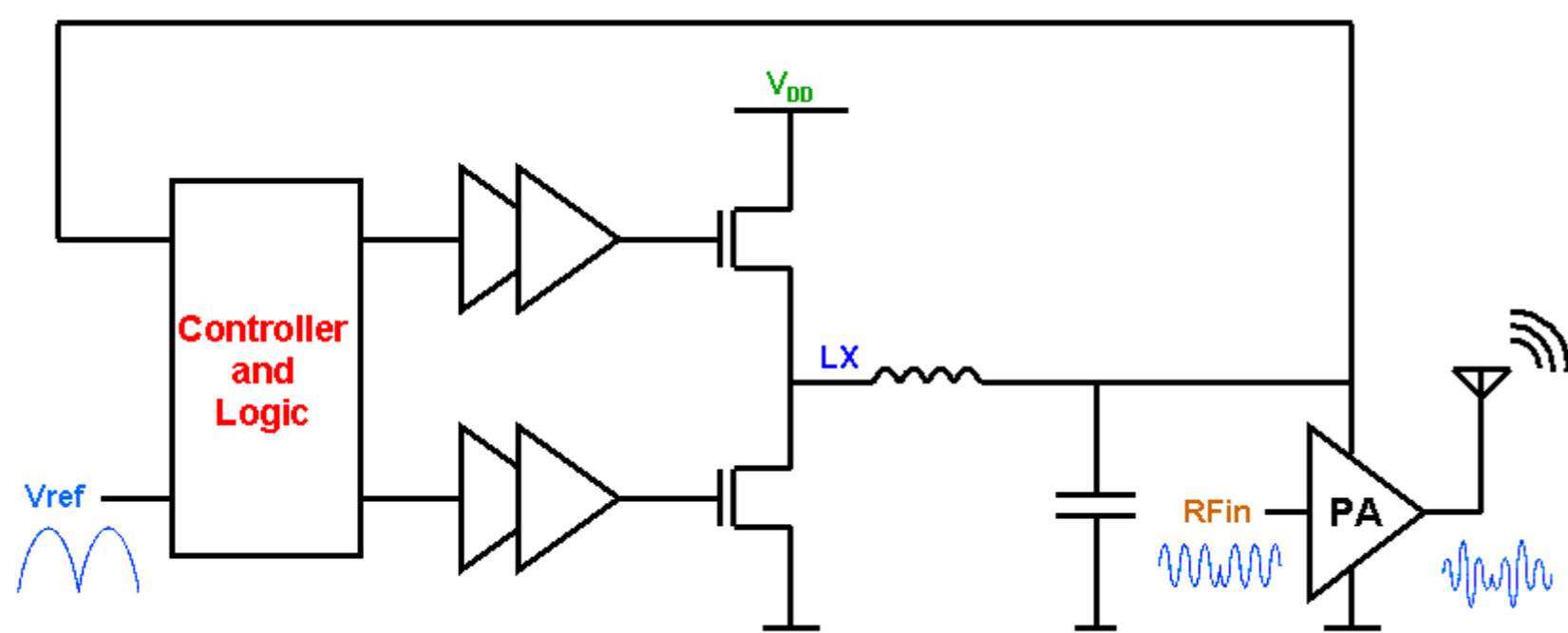


Design challenges for envelope elimination and restoration buck converter

Large BW and duty range are essential

For WCDMA, d ranges from 3 to 90% (3 decades!!!) and BW=15 MHz
 •Fs > 75 MHz
 •Very short pulse, very fast drive

$$d_{\min} T = t_r + t_f \quad (1 - d_{\max}) T > t_{d2}$$



PWM with PID controller: Good accuracy thanks to the PID. The conversion noise in the output spectrum is out of band and present around the harmonics of Fs.

Parameters evolution with switching frequency:

Transistors optimal size:

$$W_{opt} = \sqrt{\frac{I_{RMS}^2 R_{ON}^0}{f C_{MOS}^0 V^2}} \propto \frac{1}{\sqrt{f}}$$

Switching losses:

$$P_{sw} = f C_{MOS} V^2 \propto \sqrt{f} V^2$$

Ohmic losses:

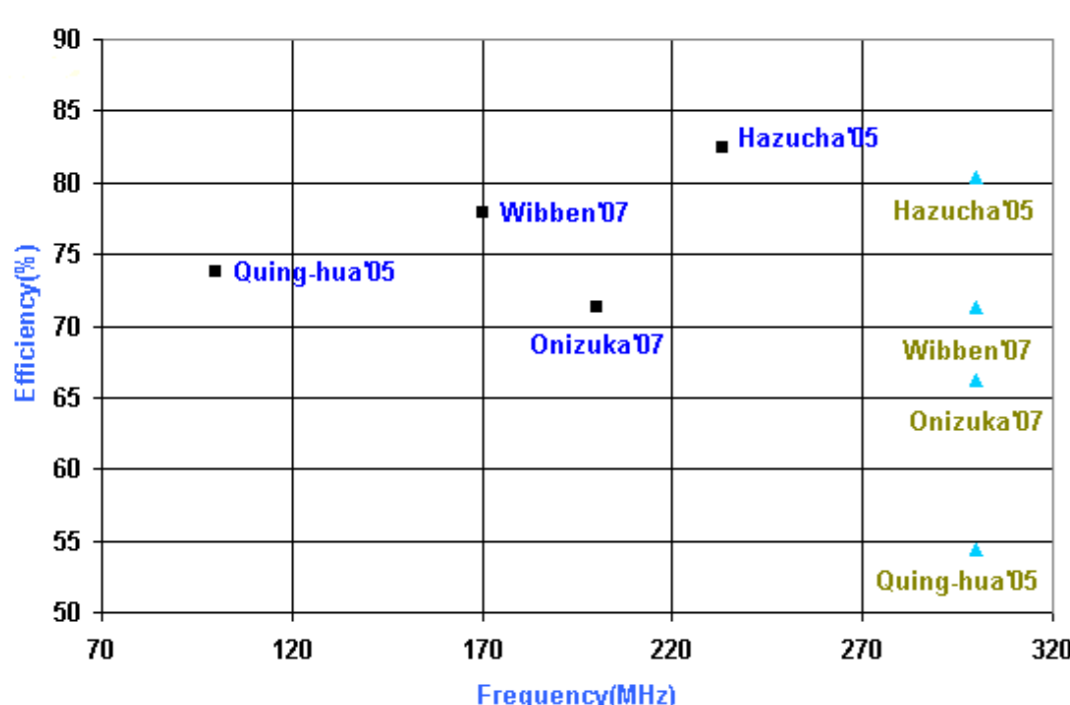
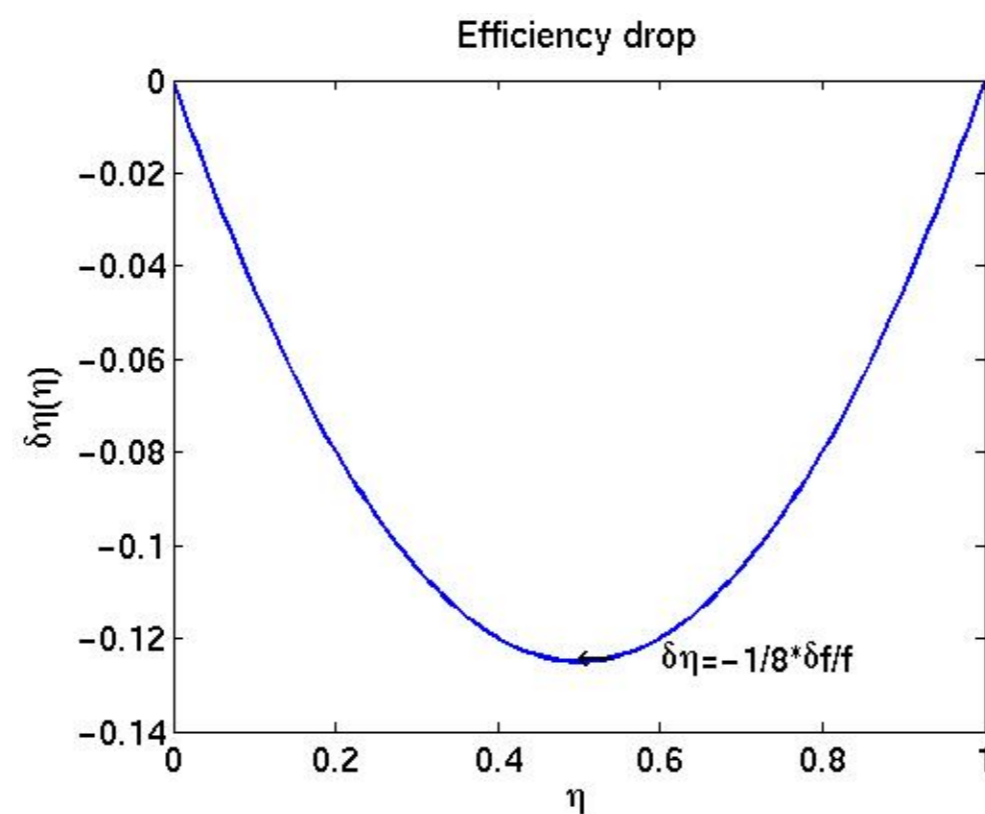
$$P_{\Omega} = R_{BRG} I_{rms}^2 \propto \sqrt{f} I_{rms}^2$$

Efficiency variation with frequency:

Efficiency drop as Fs increases:

$$\eta_{\max} = \frac{1}{1 + \frac{P_{loss}}{P_{load}}} = \frac{1}{1 + \frac{2a\sqrt{f}}{P_{load}}}$$

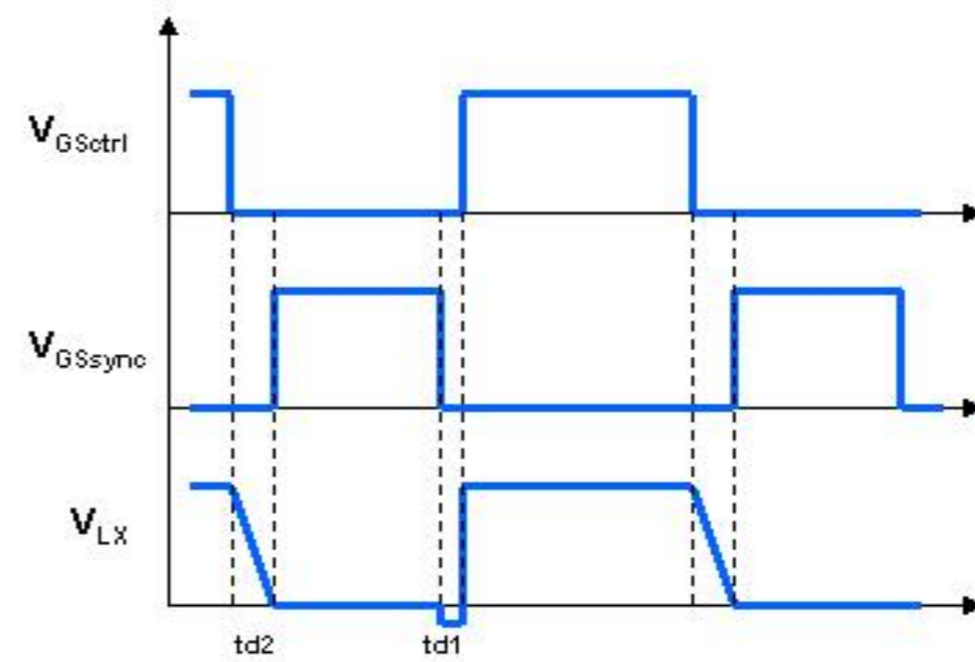
$$d\eta = -\frac{1}{2} \eta(1-\eta) \frac{df}{f}$$



Interestingly, the figure above shows that a very efficient converter exhibits a low efficiency drop when the switching frequency is increased.

Prior arts are compared for the same Fs using the equation above

Dead-time control in HF:



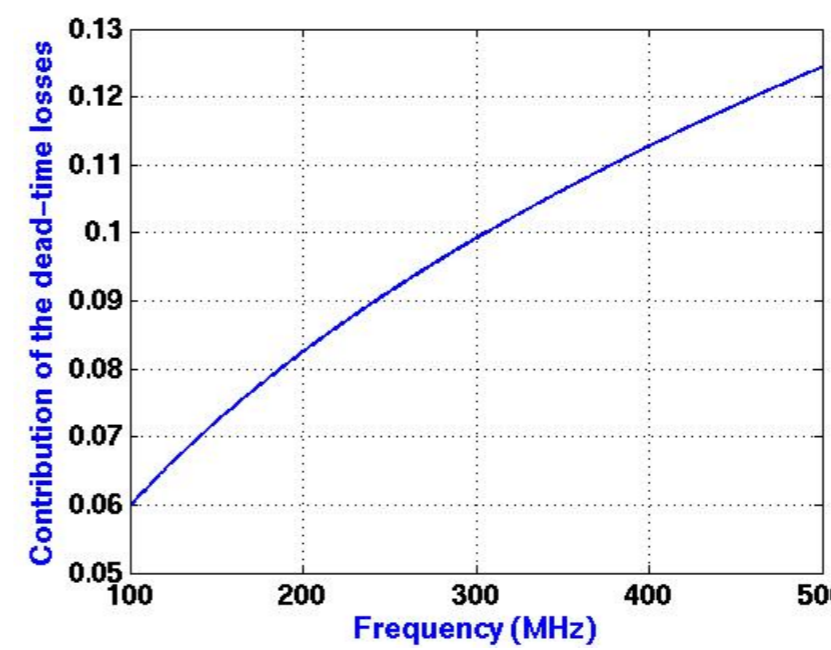
$$t_{d2} = C_{LX} \frac{V_{DD}}{I_{L,max}}$$

$$P_d = \tau_d F_s V_d I_{out} = \frac{\tau_d}{T_s} V_d I_{out}$$

•A shorter delay t_{d2} leads to a lossy discharge of C_{LX} . While a larger delay increases the losses due to the body diode.

•There is a minimum value of the total dead-time depending on the transit time

through an inverter gate for a given process, i.e. the ratio $\frac{\tau_d}{T_s}$ cannot be kept minimum while increasing the switching frequency.

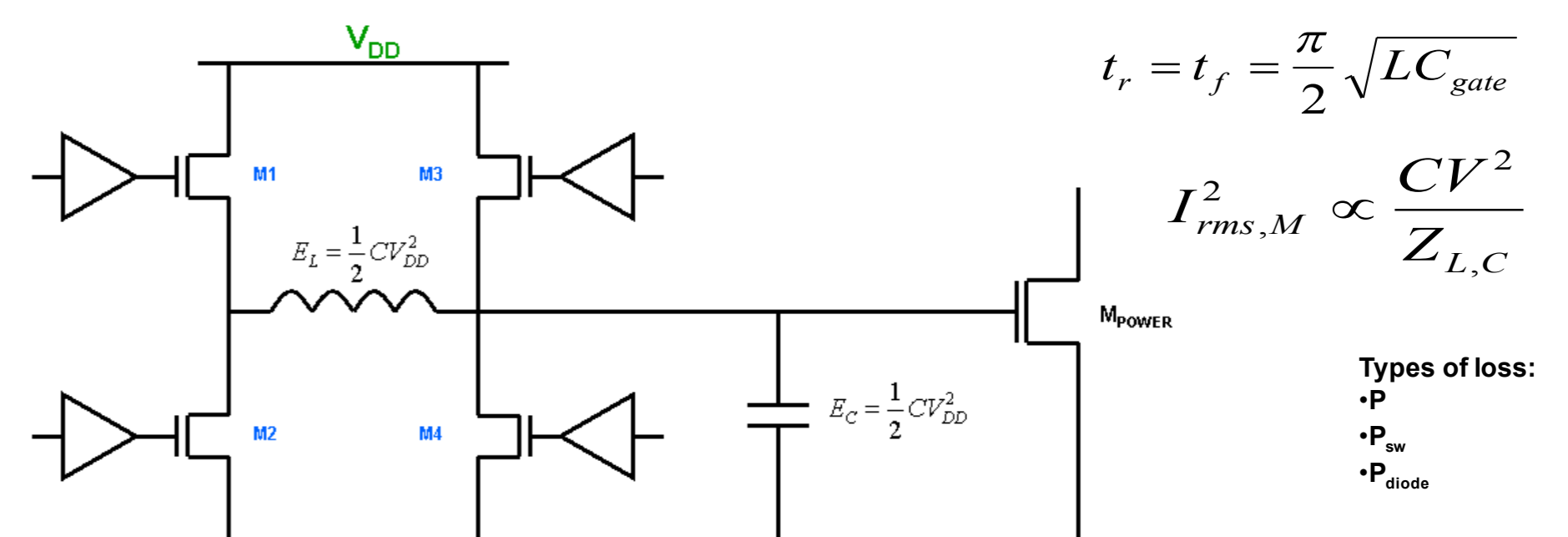


The contribution of the dead-time losses was evaluated with the following conditions:
 •Process: BiCMOS 0.25- μ m
 •The minimum achievable dead-time to perform a proper control was assumed to be 10 times the delay through an inverter gate
 •The converter operates at the optimal point where the switching losses equal the resistive losses

•With a varying loading condition like in polar modulation, an adaptive control is required to minimize the power loss.

Resonant gate drivers:

The aim is to lower the switching losses for high Fs thanks to energy recycling



$$t_r = t_f = \frac{\pi}{2} \sqrt{LC_{gate}}$$

$$I_{rms,M}^2 \propto \frac{CV^2}{Z_{L,C}}$$

Types of loss:
 •P
 •P_{sw}
 •P_{diode}

•Various types of switching are possible

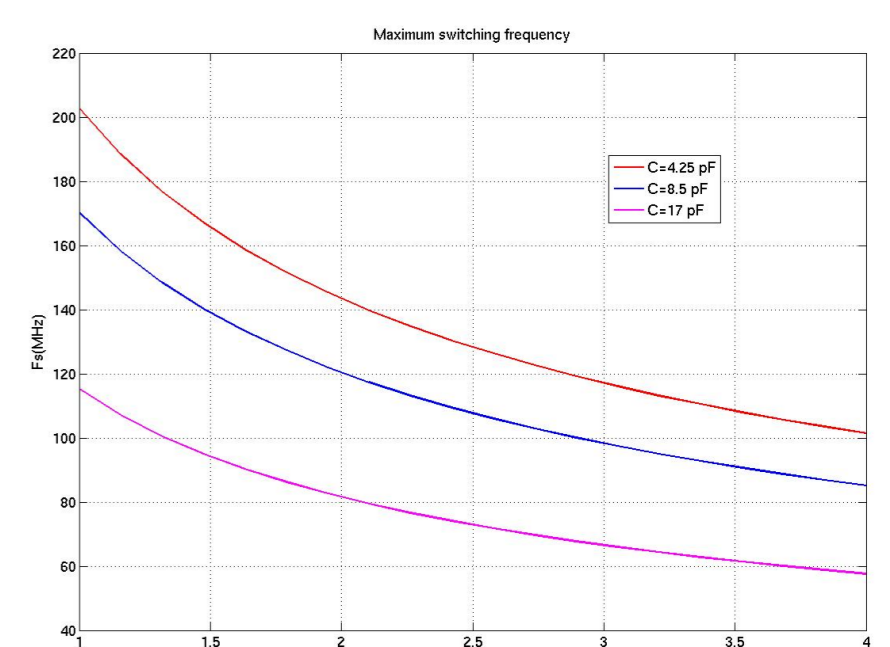
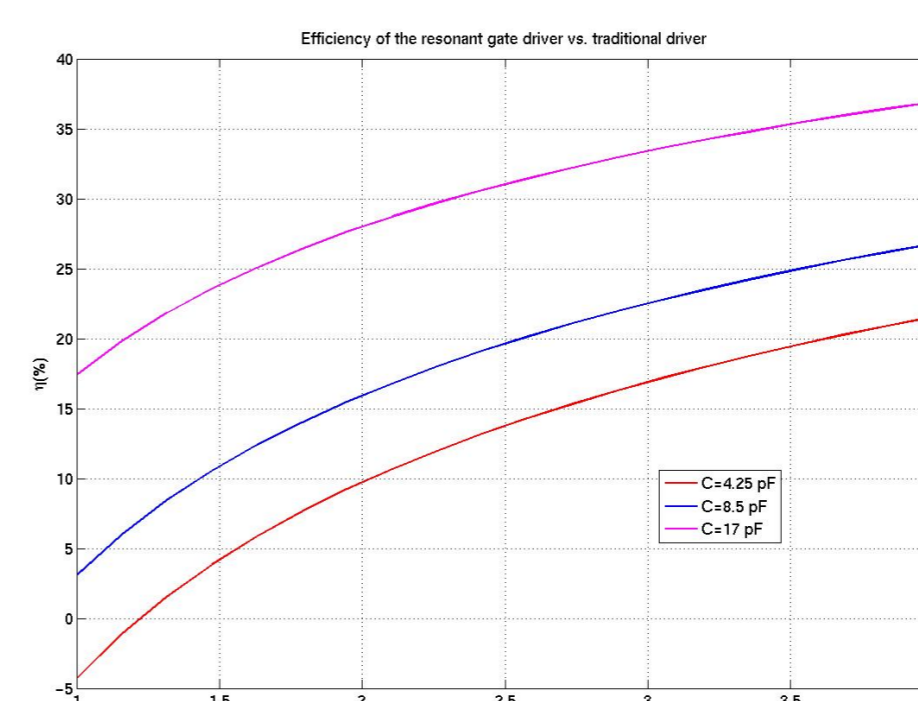
•One key parameter is the RMS current flowing through the switches, because it determines the efficiency of the resonant gate drivers compared to the traditional driver.

Efficiency of the driver

$$\frac{P_{res.dr}}{P_{trad.dr}} \propto \frac{1}{\sqrt{t_{r,f}}}$$

A low power dissipation is obtained at the cost of longer transition time.

$$\eta_{res.dr} = 1 - \frac{P_{res.dr}}{P_{trad.dr}}$$



The long transition time makes it incompatible for HF because it limits the duty cycle range and increases the ON-resistance of the switches.

L is small enough to allow the integration of the driver